### Nch 40V 10A Power MOSFET

V <sub>DSS</sub>	40V
R <sub>DS(on)</sub> (Max.)	14.3mΩ
I <sub>D</sub>	±10A
$P_D$	2W

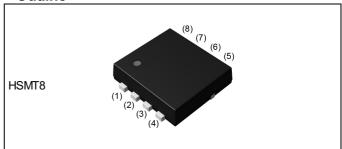
### Features

- 1) Low on resistance.
- 2) High Power Package (HSMT8).
- 3) Pb-free lead plating; RoHS compliant.
- 4) Halogen Free.

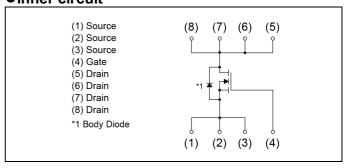
## Application

Switching

#### Outline



### ●Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	12
-	Basic ordering unit (pcs)	3000
	Taping code	ТВ
	Marking	G100GN

### ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	40	V
Continuous drain current	I <sub>D</sub>	±10	Α
Pulsed drain current	I <sub>DP</sub> *1	±40	Α
Gate - Source voltage	V <sub>GSS</sub>	±20	V
Avalanche current, single pulse	I <sub>AS</sub> *2	10	Α
Avalanche energy, single pulse	E <sub>AS</sub> *2	15.6	mJ
Power dissipation	P <sub>D</sub> *3	2	W
Junction temperature	T <sub>j</sub>	150	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	°C

### ●Thermal resistance

Parameter	Cymah al	Values			Lleit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - ambient	R <sub>thJA</sub> *3	1	62.5	-	°C/W

## ● Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymah al	Symbol Conditions		Values			
1 drameter Symbol		Conditions	Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	40	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j} I_D = 1 \text{mA}$ referenced to 25°C		-	26.2	-	mV/°C	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V	-	-	1	μA	
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA	
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 1mA$	1.2	-	2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_{j}}$	I <sub>D</sub> = 1mA referenced to 25°C	-	-4.9	-	mV/°C	
Static drain - source	D *4	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	-	11.0	14.3	C	
on - state resistance	R <sub>DS(on)</sub> *4	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	-	14.1	18.3	mΩ	
Gate resistance	$R_{G}$	f = , open drain	-	2.3	-	Ω	
Forward Transfer Admittance	Y <sub>fs</sub>  *4	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A	7.5	-	-	S	

<sup>\*1</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*2</sup> L  $^{\simeq}$  0.2mH,  $V_{DD}$  = 20V,  $R_{G}$  = 25 $\!\Omega$ , STARTING  $T_{ch}$  = 25 $\!^{\circ}\!$ C Fig.3-1,3-2

<sup>\*3</sup> MOUNTED ON A CERAMIC BOARD

<sup>\*4</sup> Pulsed

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Doramatar	Cumb of	Conditions	Values			Unit	
Parameter	Symbol Conditions		Min.	Тур.	Max.	Uniil	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	615	-		
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V	-	100	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	1	28	ı		
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq 20V, V_{GS} = 10V$	1	8.0	ı		
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = 5A	-	4.2	-		
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L \simeq 4\Omega$	-	23.1	-	ns	
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	3.2	-		

# • Gate charge characteristics $(T_a = 25^{\circ}C)$

Daramatar	Cymahal	Conditions		Values			1.1:4
Parameter	Symbol			Min.	Тур.	Max.	Unit
Total mate about	O *4		V <sub>GS</sub> = 10V	-	8.4	-	
Total gate charge	Q <sub>g</sub> *4	V <sub>DD</sub> ≈ 20V		-	4.3	-	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = 10A	V <sub>GS</sub> = 4.5V	-	1.6	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4			-	1.2	-	

## ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Doromotor	Symbol	Conditions	Values			Unit
Parameter Symbol Conditions		Min.	Тур.	Max.	Offic	
Continuous forward current	I <sub>S</sub>	T = 25°C	-	-	1.67	Α
Pulse forward current	I <sub>SP</sub> *1	T <sub>a</sub> = 25°C	1	-	40	Α
Forward voltage	V <sub>SD</sub> *4	$V_{GS} = 0V, I_S = 1.67A$	-	-	1.2	V
Reverse recovery time	t <sub>rr</sub> *4	I <sub>S</sub> = 10A, V <sub>GS</sub> =0V	-	21	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	di/dt = 100A/μs	-	12	-	nC

Fig.1 Power Dissipation Derating Curve

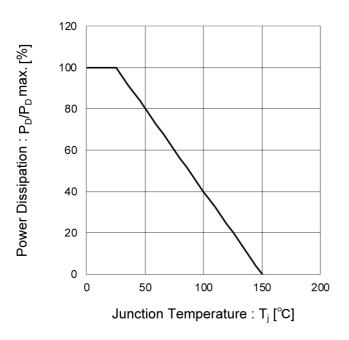
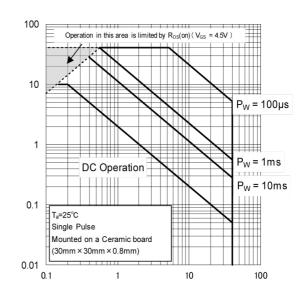


Fig.2 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

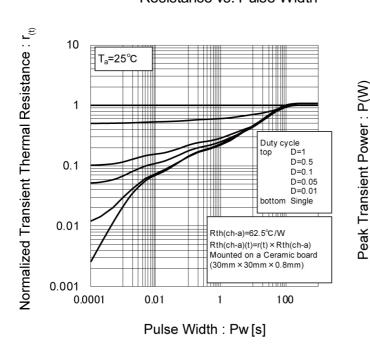
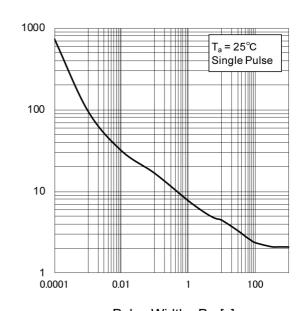


Fig.4 Single Pulse Maximum Power dissipation

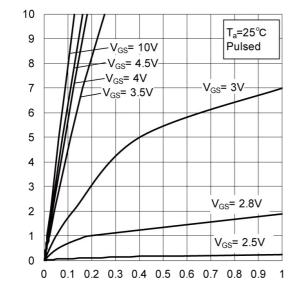


Pulse Width : Pw [s]

Drain Current : I<sub>D</sub> [A]

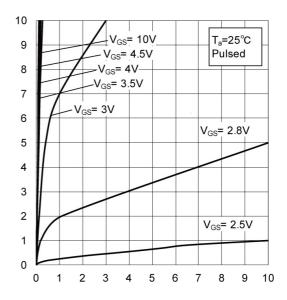
### • Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage :  $V_{DS}[V]$ 

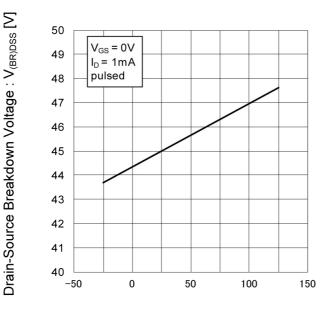
Fig.6 Typical Output Characteristics(II)



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

Fig.8 Typical Transfer Characteristics

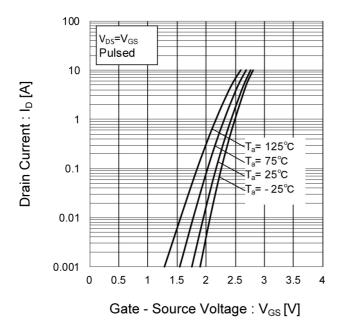
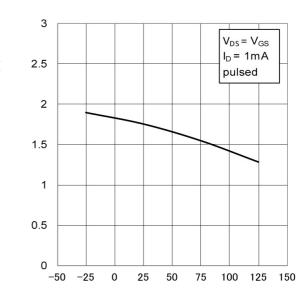


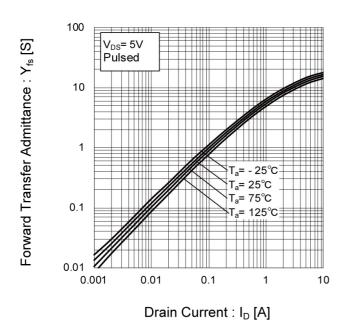
Fig.9 Gate Threshold Voltage vs. Junction Temperature



Gate Threshold Voltage: VGS(th) [V]

Junction Temperature : T<sub>j</sub> [°C]

Fig.10 Transconductance vs. Drain Current



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Fig.11 Drain Current Derating Curve

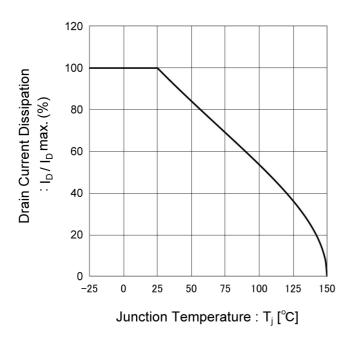
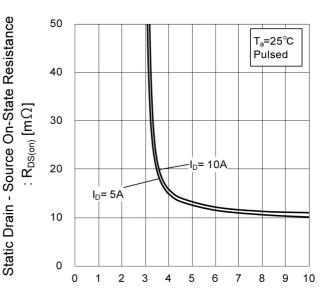
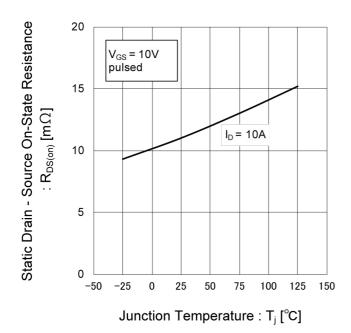


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



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Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

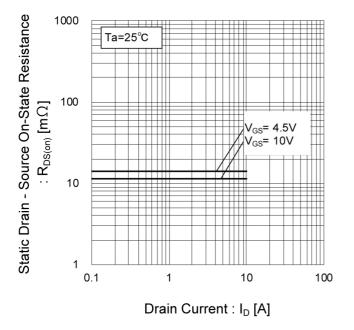


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

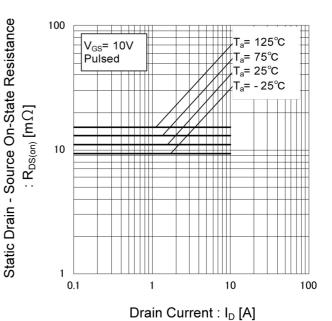


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

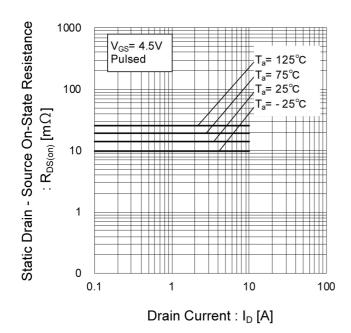
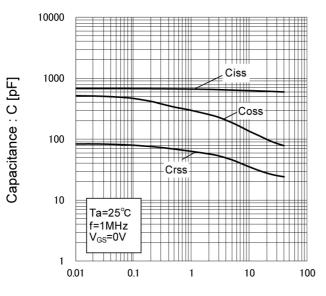


Fig.17 Typical Capacitance vs. Drain -Source Voltage



Drain - Source Voltage: V<sub>DS</sub> [V]

Fig.18 Switching Characteristics

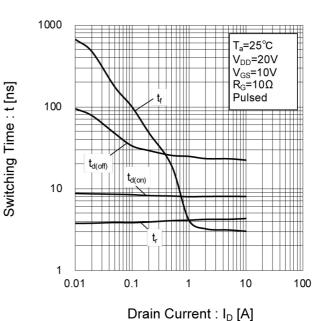
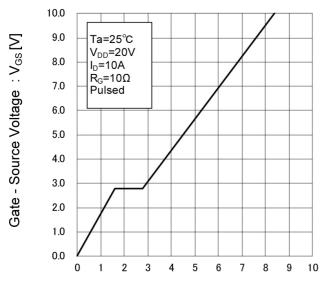
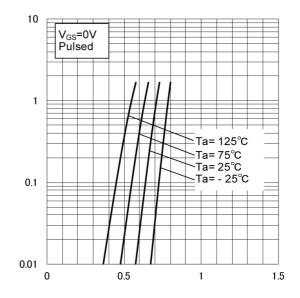


Fig.19 Dynamic Input Characteristics



Total Gate Charge: Q<sub>q</sub> [nC]

Fig.20 Source Current vs. Source Drain Voltage



Source-Drain Voltage: V<sub>SD</sub>[V]

Source Current : Is [A]

### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

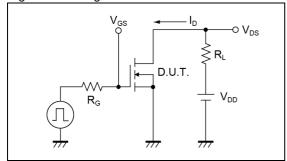


Fig.2-1 Gate Charge Measurement Circuit

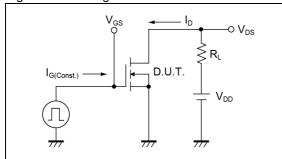


Fig.3-1 Avalanche Measurement Circuit

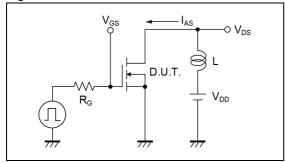


Fig.1-2 Switching Waveforms

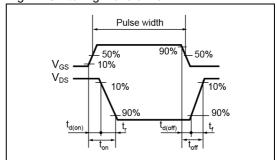


Fig.2-2 Gate Charge Waveform

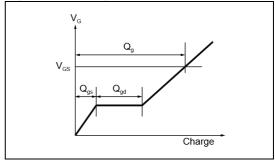
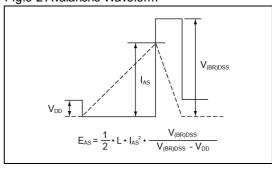


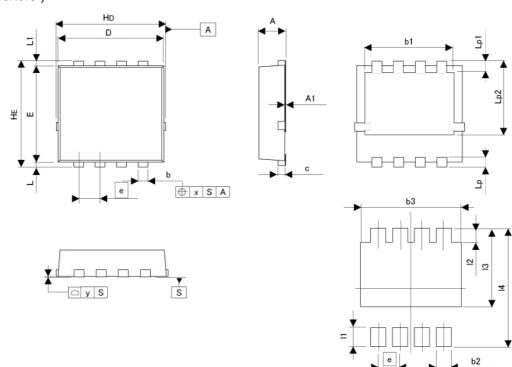
Fig.3-2 Avalanche Waveform



### Dimensions

### HSMT8

(3.3x3.3)



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIMETERS		INCI	HES
DIIVI	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
С	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
е	0.	0.65		)26
HD	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
Х	-	0.10	-	0.004
у	-	0.10	-	0.004

DIM	MILIMETERS		INC	HES
DIIVI	MIN	MAX	MIN	MAX
b2		0.47		0.019
b3	0.70	2.70	-	0.106
11	-	0.50	-	0.020
12	-	0.55	-	0.022
13	(. <b>=</b> .}	2.40	-	0.094
14	121	3.40	-	0.134

Dimension in mm/inches



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CLASSⅢ	CLASSⅢ	CLASS II b	CL ACCIII
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

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  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
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- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation (Pd) depending on Ambient temperature (Ta). When used in sealed area, confirm the actual ambient temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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For details, please refer to ROHM Mounting specification

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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
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